## **MA2J727**

### Silicon epitaxial planar type

For super high speed switching For small current rectification

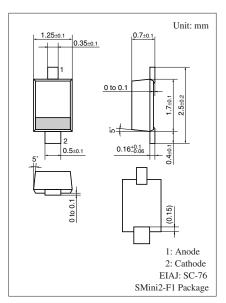
#### ■ Features

- $V_R = 50 \text{ V}$  is guaranteed
- $I_{F(AV)} = 200 \text{ mA}$  rectification is possible

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter                                   | Symbol             | Rating      | Unit |
|---------------------------------------------|--------------------|-------------|------|
| Reverse voltage                             | $V_R$              | 50          | V    |
| Repetitive peak reverse voltage             | V <sub>RRM</sub>   | 50          | V    |
| Peak forward current                        | $I_{FM}$           | 300         | mA   |
| Forward current (Average)                   | I <sub>F(AV)</sub> | 200         | mA   |
| Non-repetitive peak forward surge current * | $I_{FSM}$          | 1           | A    |
| Junction temperature                        | T <sub>j</sub>     | 150         | °C   |
| Storage temperature                         | $T_{stg}$          | -55 to +150 | °C   |

Note) \*: The peak-to-peak value in one cycle of 50 Hz sine wave (non-repetitive)



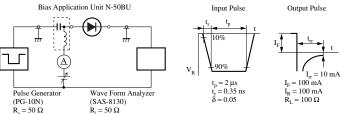
Marking Symbol: 2F

#### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

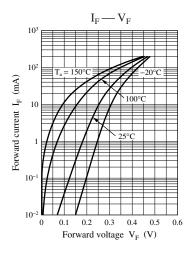
| Parameter               | Symbol          | Conditions                                 | Min | Тур | Max  | Unit |
|-------------------------|-----------------|--------------------------------------------|-----|-----|------|------|
| Reverse current         | $I_R$           | $V_R = 50 \text{ V}$                       |     |     | 200  | μΑ   |
| Forward voltage         | V <sub>F1</sub> | $I_F = 30 \text{ mA}$                      |     |     | 0.36 | V    |
|                         | V <sub>F2</sub> | $I_F = 200 \text{ mA}$                     |     |     | 0.55 | V    |
| Terminal capacitance    | C <sub>t</sub>  | $V_R = 0 \text{ V, } f = 1 \text{ MHz}$    |     | 30  |      | pF   |
| Reverse recovery time * | t <sub>rr</sub> | $I_F = I_R = 100 \text{ mA}$               |     | 3.0 |      | ns   |
|                         |                 | $I_{rr} = 10 \text{ mA}, R_L = 100 \Omega$ |     |     |      |      |

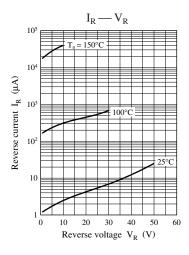
- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.
  - This product is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.
  - 3. Absolute frequency of input and output is 1 GHz.

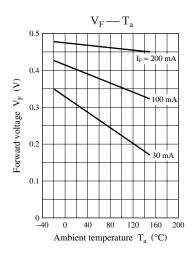
4. \*: t<sub>rr</sub> measurement circuit

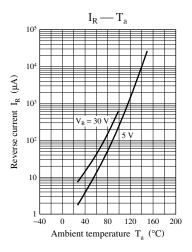


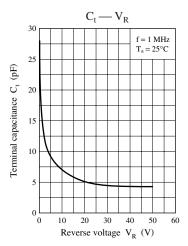
# **Panasonic**











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